

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A semiconductor device having a lead electrode , a case electrode having a projection part around its periphery, and a semiconductor chip having a rectification function and connected electrically between said lead electrode and said case electrode through soldering connection members, wherein an electrically conductive plate is provided between said semiconductor chip and said lead electrode through said soldering connection members, wherein said electrically conductive plate has a coefficient of linear expansion smaller than that of said case electrode and maximum width smaller than a maximum width of said semiconductor chip, wherein said lead electrode has a first portion and a second portion, said first portion being formed between said second portion and the electrically conductive plate, wherein said first portion is wider than said second portion, and wherein said first portion is joined to said electrically conductive plate through one of said soldering connection members.

2. (Previously Presented) A semiconductor device according to claim 1, wherein the coefficient of linear expansion of said electrically conductive plate is equal to or larger than 50 % of that of said semiconductor chip.

3. (Original) A semiconductor according to claim 1, wherein the strength of said electrically conductive plate is larger than that of said case electrode.

4. (Withdrawn) A semiconductor device according to claim 1, wherein said case electrode has a layer structure having a metal containing copper through a metal containing iron.

5. (Previously Presented) A semiconductor device according to claim 1, wherein said electrically conductive plate has a layer structure of copper-iron alloy-copper, and the iron alloy containing a 30 % to 50 % with Ni remainder Fe, or a 20 % to 40 % with Ni-50 % to 60 % with Fe remainder Co.

6. (Withdrawn) A semiconductor device according to claim 1, wherein said electrically conductive plate is made of an iron alloy containing a 30 % to 50 % with Ni remainder Fe or a 20 % to 40 % Ni-50 % to 60 % with Fe remainder Co.

7. (Withdrawn) A semiconductor device according to claim 1, wherein said electrically conductive plate is an electrically conductive plate made of Mo as a main constituent element and having a thickness equal to or larger than 100 % of that of said semiconductor chip.

8. (Withdrawn) A semiconductor device according to claim 1, wherein said electrically conductive plate is an electrically conductive plate made of W as a main

constituent element and having a thickness equal to or larger than 100 % of that of said semiconductor chip.

9. (Currently Amended) A semiconductor device having a lead electrode , a case electrode having a projection part around its periphery, and a semiconductor chip having a rectification function and connected electrically between said lead electrode and said case electrode through soldering connection members, wherein an electrically conductive plate is provided between said semiconductor chip and said lead electrode through said soldering connection members, wherein said electrically conductive plate has a coefficient of linear expansion smaller than that of said case electrode, and a width of said electrically conductive plate is equal to or smaller than 90 % and equal to or larger than 50 % of that of said semiconductor chip, wherein said lead electrode has a first portion and a second portion, said first portion being formed between said second portion and the electrically conductive plate, wherein said first portion is wider than said second portion, and wherein said first portion is joined to said electrically conductive plate through one of said soldering connection members.

10. (Currently Amended) A semiconductor device having a lead electrode , a case electrode having a projection part around its periphery, and a semiconductor chip having a rectification function and connected electrically between said lead electrode and said case electrode through a solder, wherein an electrically conductive plate is provided between said semiconductor chip and said lead electrode through said solder, wherein said electrically conductive plate has a

coefficient of linear expansion smaller than that of said case electrode and maximum width smaller than a maximum width of said semiconductor chip, no electrically conductive plate is provided between said semiconductor chip and said case electrode, and each width of said lead electrode and said electrically conductive plate is smaller than that of said semiconductor chip, and the solder between said semiconductor chip and said electrically conductive plate is formed in such a way that a width of the side end of said electrically conductive plate is smaller than that of the side end of said semiconductor chip, wherein said lead electrode has a first portion and a second portion, said first portion being formed between said second portion and the electrically conductive plate, wherein said first portion is wider than said second portion, and wherein said first portion is joined to said electrically conductive plate through one of said soldering connection members.

11. (Currently Amended) A semiconductor device having a lead electrode , a case electrode having a projection part around its periphery, and a semiconductor chip having a rectification function and connected electrically between said lead electrode and said case electrode through a solder, wherein an electrically conductive plate is provided between said semiconductor chip and said lead through said solder, wherein said electrically conductive plate has a coefficient of linear expansion smaller than that of said case electrode and maximum width smaller than a maximum width of said semiconductor chip, no electrically conductive plate is provided between said semiconductor chip and said case electrode, and each width of said lead electrode and said electrically conductive plate is smaller than that of said semiconductor chip, and the solder between said semiconductor chip and said

electrically conductive plate is formed in such a way that a width of the side end of said electrically conductive plate is smaller than that of the side end of said semiconductor chip, and the solder between said semiconductor chip and said case electrode is formed in such a way that a width of the side end of said semiconductor chip is smaller than that of the side end of said case electrode, wherein said lead electrode has a first portion and a second portion, said first portion being formed between said second portion and the electrically conductive plate, wherein said first portion is wider than said second portion, and wherein said first portion is joined to said electrically conductive plate through one of said soldering connection members.

12. (New) A semiconductor device according to claim 1, wherein said first portion of said lead electrode is embedded in said one of said soldering connection members formed between said first portion and said electrically conductive plate.

13. (New) A semiconductor device according to claim 1, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

14. (New) A semiconductor device according to claim 12, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

15. (New) A semiconductor device according to claim 9, wherein said first portion of said lead electrode is embedded in said one of said soldering connection members formed between said first portion and said electrically conductive plate.

16. (New) A semiconductor device according to claim 9, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

17. (New) A semiconductor device according to claim 15, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

18. (New) A semiconductor device according to claim 10, wherein said first portion of said lead electrode is embedded in said one of said soldering connection members formed between said first portion and said electrically conductive plate.

19. (New) A semiconductor device according to claim 10, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

20. (New) A semiconductor device according to claim 18, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

21. (New) A semiconductor device according to claim 11, wherein said first portion of said lead electrode is embedded in said one of said soldering connection members formed between said first portion and said electrically conductive plate.

22. (New) A semiconductor device according to claim 11, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.

23. (New) A semiconductor device according to claim 21, wherein said first and second portions form a T configuration with the first portion being substantially parallel to the electrically conductive plate and the second portion being substantially perpendicular to the electrically conductive plate.